

Released

X-band Diode Limiter

Model No. NJS6930A

Copyright©**Nisshinbo Micro Devices Inc.
Microwave Business Headquarters**

-Notice of Proprietary Information-

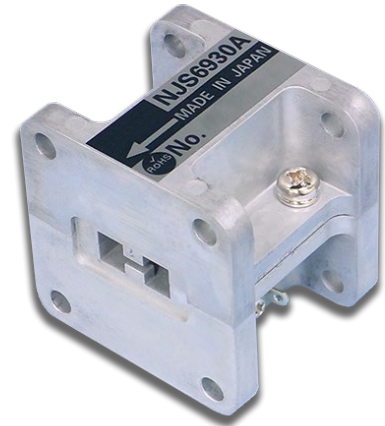
This document and its contents are proprietary to Nisshinbo Micro Devices Inc.
This publication and its contents may not be reproduced or distributed for any other purpose
without the written permission of Nisshinbo Micro Devices Inc.
Those specifications listed in this document are subject to change at any time.

■ GENERAL DESCRIPTION

NJS6930A is designed for the high power limiter of radar system.

It features a small size operable at any frequency between 9.30GHz and 9.50GHz.

This diode limiter consists of the two stage limiter diodes. And insertion loss can be controlled for STC function by the external bias current, which flows the second limiter diode.



■ ABSOLUTE MAXIMUM RATINGS

PARAMETERS	MINIMUM	MAXIMUM	UNITS
Maximum handling power	-	30	kW
Ambient temperature	-30	+90	°C
RF pulse width	-	1.5	μs
Bias current	-	5	mA

■ ELECTRICAL CHARACTERISTICS < at 25 °C >

PARAMETERS	MINIMUM	MAXIMUM	UNITS	
V.S.W.R. (Note 1,3)	-	1.5	-	
Insertion loss (Note 1,3)	-	1.5	dB	
Flat leakage power (Note 2,3)	-	150	mW	
Spike leakage power (Note 2,3)	-	600	mW	
Recovery to -3dB (Note 2,3)	-	0.5	μs	
Variable attenuation range (Note1,3)				
	Iatt= 10 uA	6	12	dB
	Iatt= 1 mA	28	34	dB

Note 1: Measured at power level 0.1mW CW.

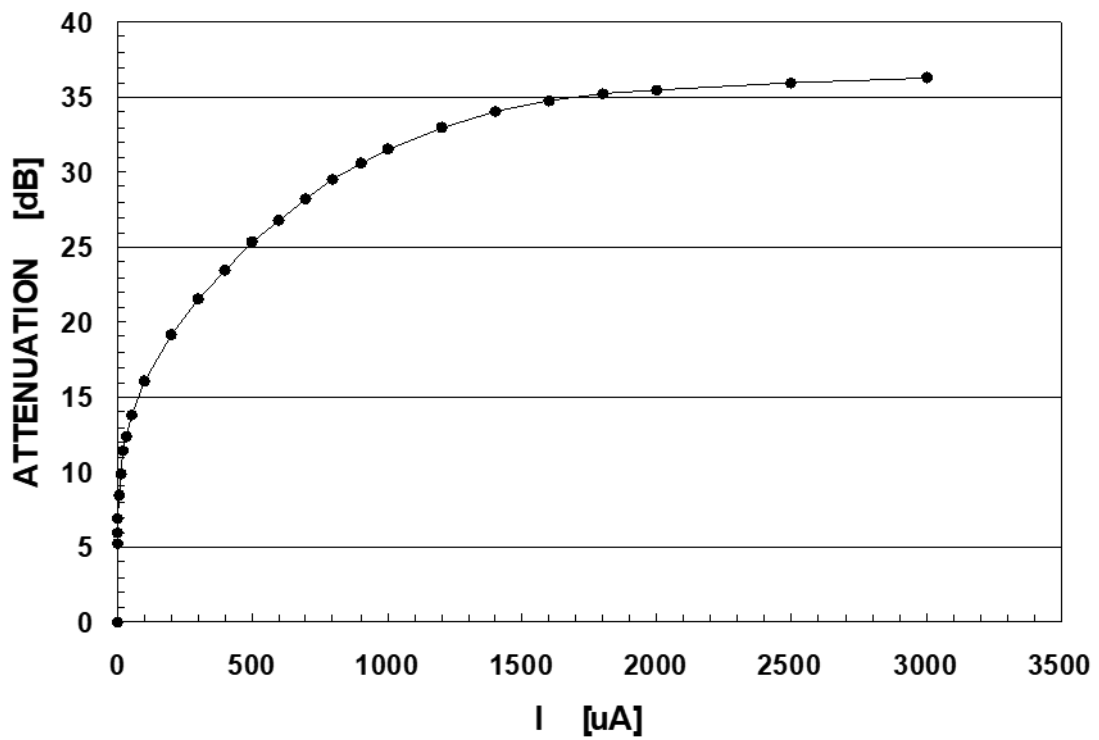
Note 2: Measured at power level 3kW, 1.0μs pulse width and 1000pps.

Note 3: Measured at frequency 9.40GHz.

* Above Specifications are subject to change without notice.

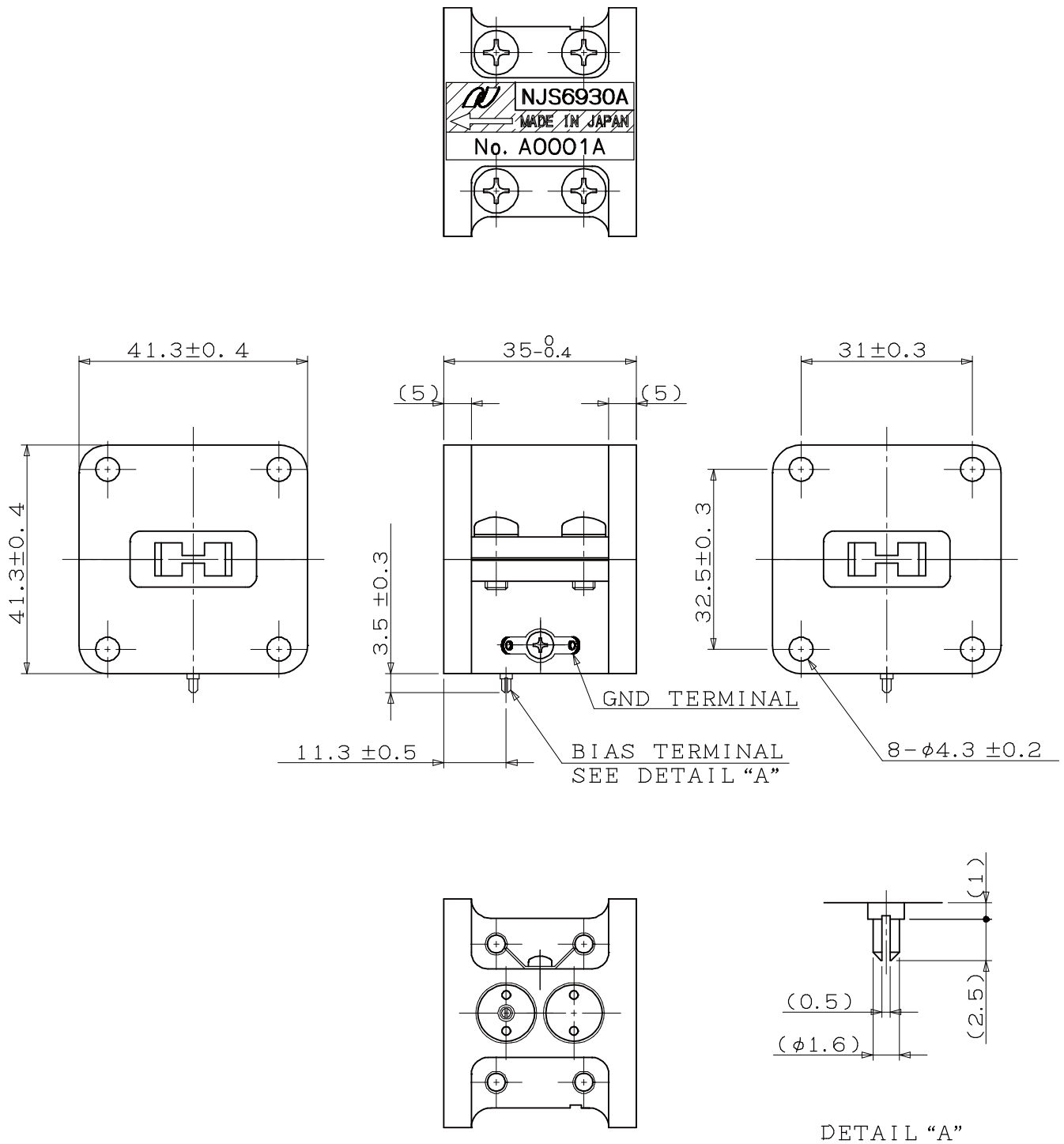
NJS6930A ATTENUATION

f=9410MHz, P=-10dBm



* Above Specifications are subject to change without notice.

■ OUTLINE



(Dimensions are expressed in "mm".)

* Above Specifications are subject to change without notice.

